

Title (en)

METHOD AND APPARATUS FOR DETERMINING PROCESSING CHAMBER CLEANING OR WAFER ETCHING ENDPOINT

Title (de)

VERFAHREN UND APPARAT ZUR BESTIMMUNG DES ENDZEITPUNKTES BEI DER SÄUBERUNG EINES BEARBEITUNGSRAUMES ODER DER ÄTZUNG EINES HALBLEITERWAFERS

Title (fr)

PROCEDE ET APPAREIL PERMETTANT DE DETERMINER LA FIN DU NETTOYAGE D'UNE CHAMBRE DE TRAITEMENT OU LA FIN DE LA GRAVURE D'UNE TRANCHE

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Application

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Abstract (en)

[origin: WO9964814A1] The gas withdrawn from a silicon wafer processing chamber, during wafer etching or chamber cleaning with a fluoride free radical-containing plasma, is analyzed optically. The apparatus consists of an infrared radiation source (10) mounted in a holder (12), to which is attached a heat sink (14). The holder (12) is mounted upon a source mirror housing (16), which contains a collimating mirror (18) supported on a source mirror holder (20). The filter sensor unit includes an endpoint instrument assembly mounting plate (22), which is mounted upon a detector mirror housing (24) and in turn contains detector focussing mirror (26) supported upon a detector mirror holder (28).

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